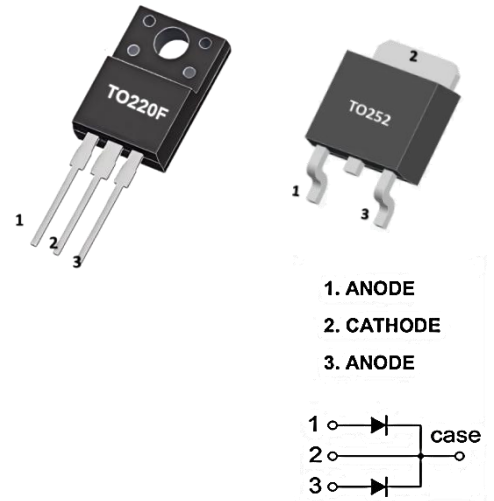


DESCRIPTION

The MBR(D/F)10200CS meet the ROHS and Green Product requirement with full function reliability approved.

FEATURE

- * Schottky Barrier Chip
- * Guard Ring Die Construction for Transient Protection
- * Low Power Loss,High Efficiency
- * High Surge Capability
- * High Current Capability and Low Forward Voltage Drop
- * For Use in Low Voltage, High Frequency Inverters,Free Wheeling, and Polarity Protection Applications



ABSOLUTE MAXIMUM RATINGS(TA=25°C, unless otherwise specified.)

SYMBOL	PARAMETER		VALUE	UNIT
VRRM	Peak repetitive reverse voltage		200	V
VRWM	Working peak reverse voltage		200	V
VR	DC blocking voltage		200	V
VR(RMS)	RMS reverse voltage		140	V
IO	Average rectified output current		10 (5*2)	A
IFSM	Non-Repetitive peak forward surge current(8.3ms half sine wave)		100*2	A
Tj	Junction temperature		175	°C
Tstg	Storage temperature		-55~+150	°C
RθJA	Thermal Resistance fromJunction to Ambient	TO-252	110	°C/W
		TO-220F	60	
RθJC	Thermal Resistance From Junction To Case	TO-252	6	°C/W
		TO-220F	4	

Notes:Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (TA=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNIT
Reverse voltage	V(BR)	IR=0.2mA		200			V
Reverse current	IR	VR=200V				50	μA
Forward voltage	VF1	IF=3A	Tj=25°C		0.82		V
	VF2	IF=5A	Tj=25°C			0.95	V
	VF3	IF=10A	Tj=25°C			1.00	V
Typical total capacitance	Ctot	VR=5V, f=1MHz			50		pF

*Pulsetest:pulsewidth ≤ 300μs,dutycycle ≤ 2.0%.

■ TYPICAL CHARACTERISTICS

